



Features

- 300 Watts Peak Pulse Power per Line ($t_p = 8/20\mu s$)
- Bidirectional Configuration
- Protects One Power or I/O Port
- ESD Protection > 40 kilovolts
- Low Clamping Voltages



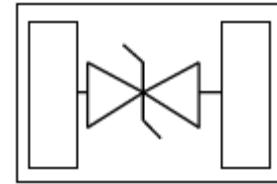
DFN1006

IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD) : $\pm 30kV$ (air), $\pm 30kV$ (contact)
- IEC 61000-4-4 (EFT) :40A (5/50ns)
- IEC 61000-4-5(Surge): 8A, 8/20 μs

Applications

- Ethernet - 10/100/1000 Base T
- Cellular Phones
- Handheld - Wireless Systems
- Personal Digital Assistant (PDA)
- USB Interface

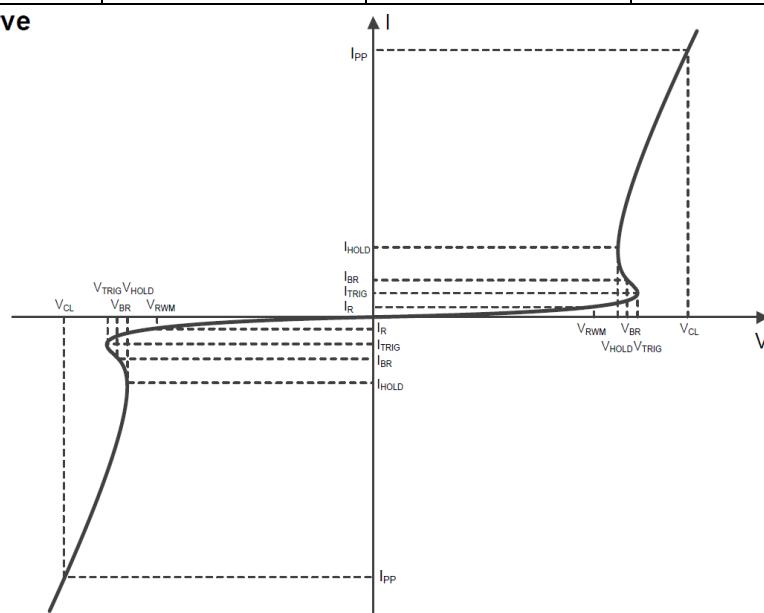


Electrical Parameters

Parameter	Symbol	Value	Units
Peak pulse power ($t_p=8/20\mu s$)	P_{PP}	300	Watts
Operating Temperature	T_J	-55°C ~ 125°C	°C
Storage Temperature	T_{STG}	-55°C ~ 150°C	°C

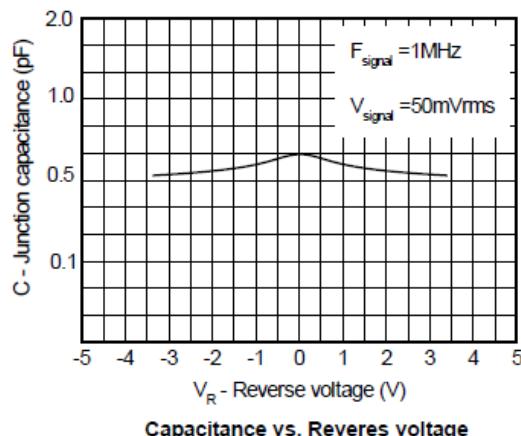
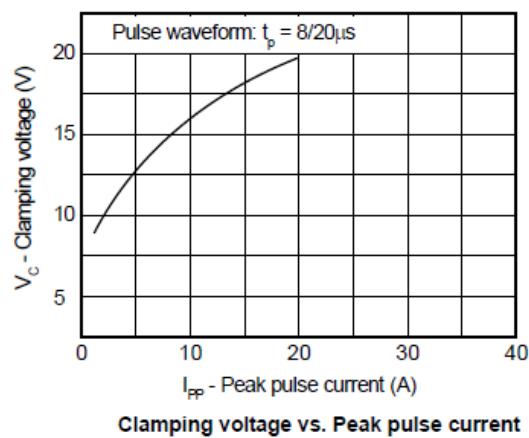
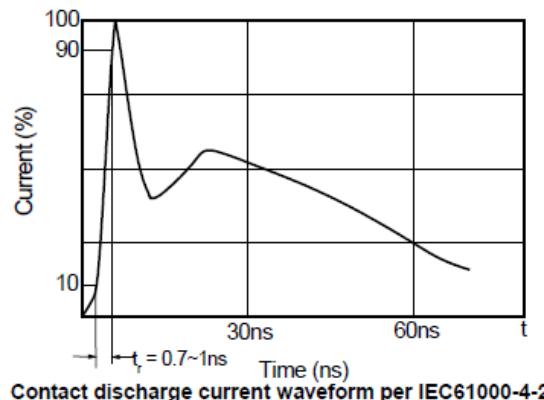
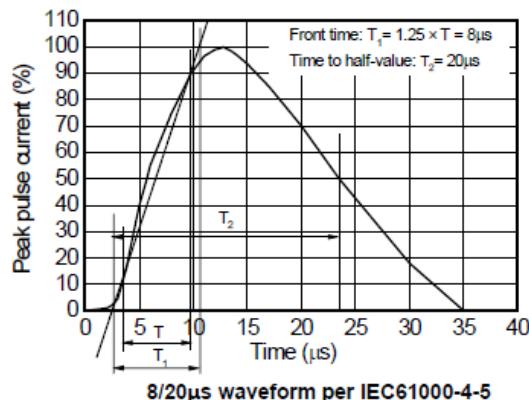
Electrical performance curve

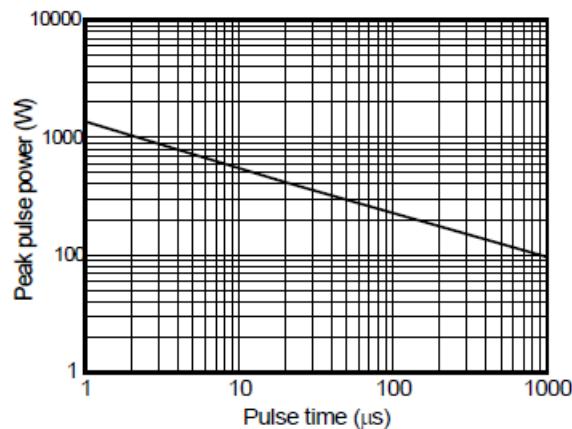
V_{RWM} Reverse stand-off voltage
 I_R Reverse leakage current
 V_{CL} Clamping voltage
 I_{PP} Peak pulse current
 V_{TRIG} Reverse trigger voltage
 I_{TRIG} Reverse trigger current
 V_{BR} Reverse breakdown voltage
 I_{BR} Reverse breakdown current
 V_{HOLD} Reverse holding voltage
 I_{HOLD} Reverse holding current



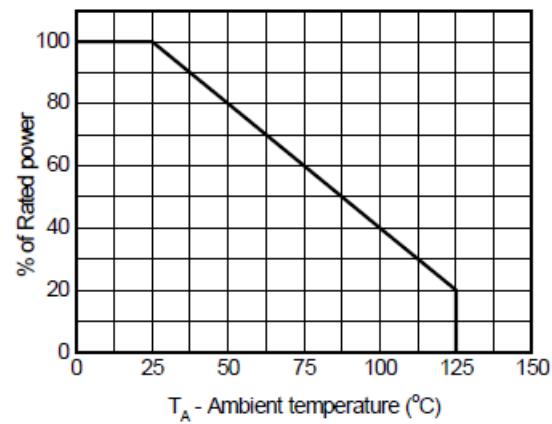
Ratings and characteristic curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Max	Units
Reverse Stand-off Voltage	V_{RWM}	Pin2 to 1/Pin1 to 2		24	V
Reverse Breakdown Voltage	$V_{BR}(\text{min})$	$I_z=1\text{mA}$	25		V
Reverse Leakage Current	$I_R(\text{max})$	@ V_{RWM}		0.5	μA
Clamping Voltage	V_C	$I_{PP}=8\text{A}$ $t_p=8/20\mu\text{s}$		40	V
Peak Pulse Current	I_{PP}	$t_p=8/20\mu\text{s}$	8		A
Junction Capacitance	$C_{I/O}$	Pin capacitance to GND. $V_{dc}=0\text{V}$, $f=1\text{MHz}$		45	pf

Typical Characteristics




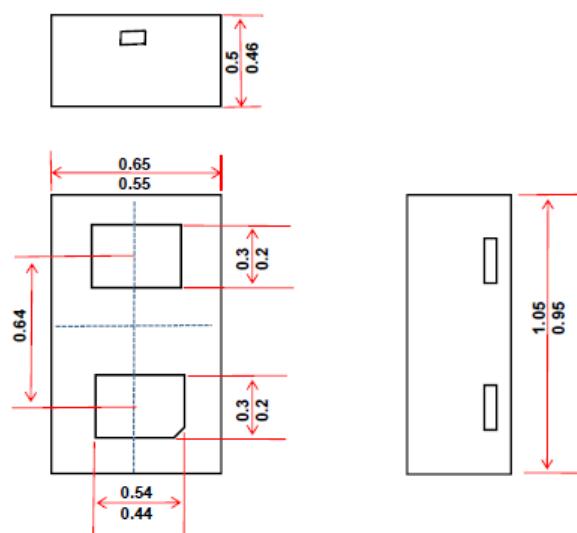
Non-repetitive peak pulse power vs. Pulse time



Power derating vs. Ambient temperature

Dimensions

DFN1006



Recommended Mounting Pad Layout Unit:mm

